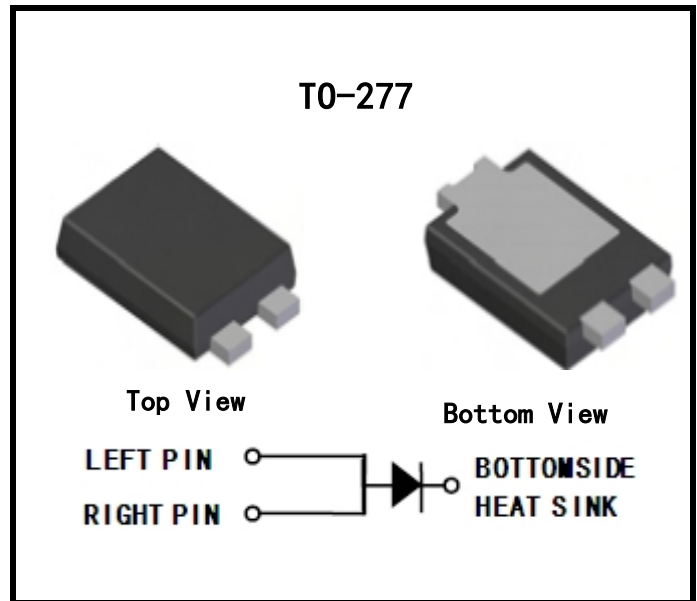


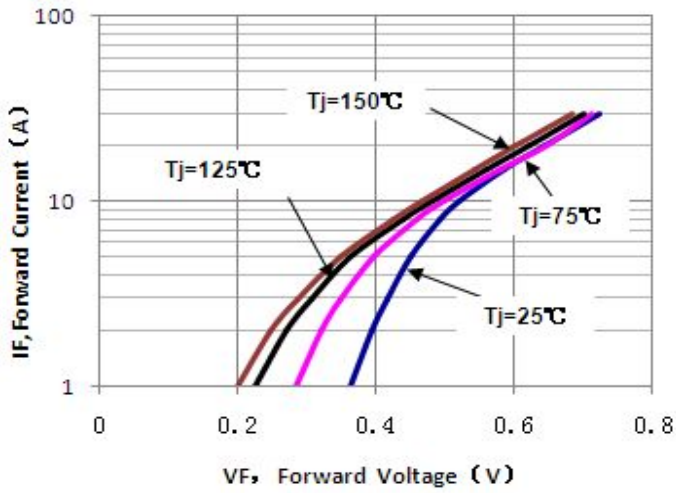
**Ultra Low VF=0.46V at IF=5A**
**FEATURES**

- \* Schottky Barrier Chip
- \* Guard Ring Die Construction for Transient Protection
- \* Low Power Loss, High Efficiency
- \* High Surge Capability
- \* High Current Capability and Low Forward Voltage Drop
- \* For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications

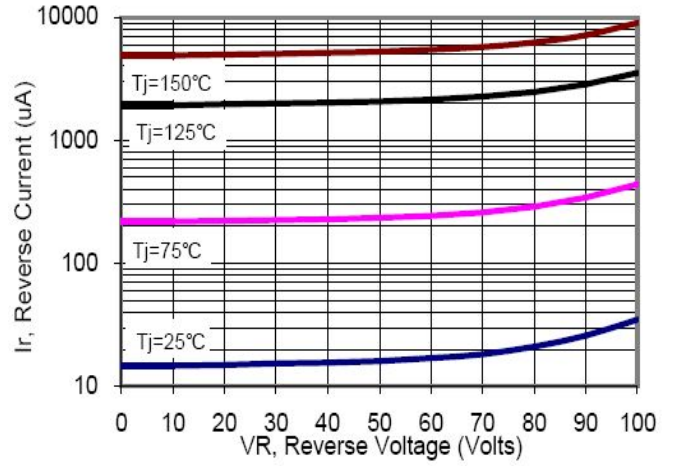
**PACKAGE**

**ELECTRICAL CHARACTERISTICS (Tamb=25°C)**

Characteristic	Symbol	Value		Unit
Peak Repetitive Reverse Voltage	$V_{RRM}$	80		V
DC Blocking Voltage	$V_R$	80		
Average Rectified Output Current	$I_{F(AV)}$	20		A
Peak Forward Surge Current 8.3ms single half sine-wave superimposed on rated load (JEDEC method)	$I_{FSM}$	280		A
Maximum Instantaneous Forward Voltage @IF=5A, TC=25°C @IF=5A, TC=125°C @IF=10A, TC=25°C @IF=10A, TC=125°C @IF=20A, TC=25°C @IF=20A, TC=125°C	$V_F$	TYP.	MAX.	V
		0.46	0.5	
		0.38	0.41	
		0.52	0.55	
		0.44	0.48	
		0.61	0.66	
0.57	0.62			
Peak Reverse Current @TA=25 °C	$I_R$	0.3		mA
at Rated DC Blocking Voltage @TA=125°C		50		
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to +150		°C
Typical Junction Capacitance	$C_J$	600		pF
Maximum Thermal Resistance	$\theta_{JA}$	31		°C/W
	$\theta_{JM}$	4		

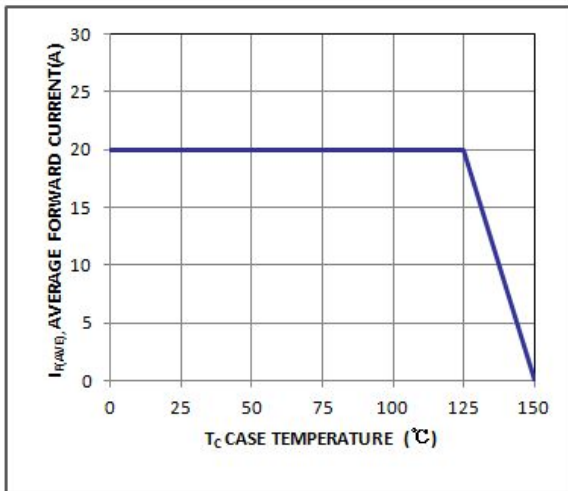
**Characteristics Curves**



**Typical Forward Voltage Per Diode**

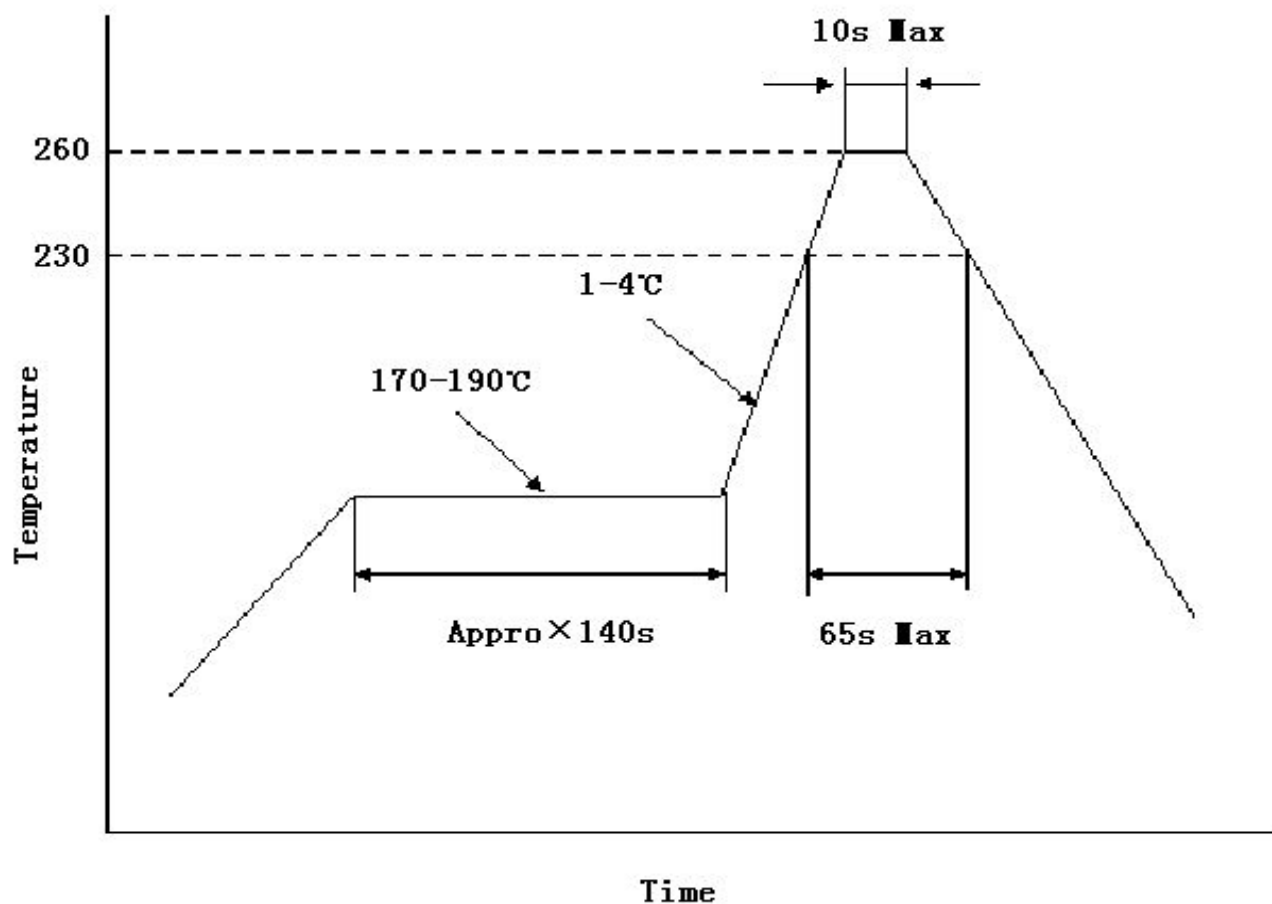


**Typical Reverse Current Per Diode**



**Average Forward Forward Current vs. Case Temperature Per Diode**

■ Reflow Soldering Temperature Profile



**TO-277 MECHANICAL DATA**

UNIT: mm

SYMBOL	MIN	MAX	SYMBOL	MIN	MAX
A	1.05	1.2	e	1.65	1.95
A2	0.3	0.45	E	6.3	6.6
b1	0.8	1	E1	5.3	5.8
b2	1.7	1.9	E2	3.1	3.6
b3	0.7	0.9	L	0.5	0.7
D	3.85	4.3	L1	0.5	0.7
D2	2.9	3.3	L2	0.8	1.1
W	1.1	1.4	h	0.1	0.2
W1	0.3	0.5			

